



e t d h e t c t a f e a t e f c e a i t a d h e  
 i - i t a g h f T F C D c a e d b h e e e c t i c e d i -  
 a h e t h e c e i h a S A a d i a h a t i d h e d  
 i h a h a t e .

L i - a d L a e t i c h [ 2 ] i - e i g a d h e c e a i -  
 f h e e e c t i c e d - i - d c e d t a i t i - a g e e t ,  
 i - i a t h e h e e t t d b t f a d h e d S A  
 a d i a . T h e d e t a d h a t h e t a i t i - a  
 t - h i c e . D i - g h e t h a h e a g e  
 g a d a i - c e a e , T F C D f i c b i c  
 e a \* c e a d a d i f f e e t i t i - h e c e . T h e e i t  
 h a e e h e b f a c e i - h e f e c i t . U h f h e  
 e d i - c e a e , h e a d i - a f h e T F C D i - c e a e , b t  
 t e c i t a a d i - a \*\* , f h e d e f h e c e  
 h i c e h . A t a > a \*\* , h e T F C D c h a g e i - t a t h e  
 d a i - ( S D ) ; h e b e c t e i - t c i c a e t ,  
 T h a e d - i - d c e d a b e T F C D i - h e e t i c a d  
 g e e t f a h e t h e c e h a t c h a c a d i - t  
 e : h e i - i - a \* e b e h i c h a T F C D  
 e b i - a b e i h e h e c t t h e h e t b e d  
 c e g a t f a t e c i t a e , a d a a i -  
 e a \*\* a b e h i c h h e T F C D i - a b e i h e h e c t  
 t a S D . T h e t h i - h e T F C D g h a e  
 c t e d b d i f f e e t c t u b i t t h e f e e e e g  
 f h e a [ 2 , 3 ] . T h e t h i - h e a \* < a < a \*\* , i -  
 c t e d a i - b ( a ) d i e e c t i c c h i - g e e g f  
 h e a i - t h e S A h a e a d h e e e c t i c e d , ( b )  
 e a t e e g f d e f a i t i - h e T F C D , a d ( c )  
 e e g f d i - t i t a d i - h e f e c i t i - h e b  
 f h e a d i a a t h e f a c e f h e c e . D i - g  
 h e e c d h i a > a \*\* , h e f a c e a c h i - g f h e  
 e c i t a e a t h e b d i - g h a d f h e c e b e g i -  
 t h a a i - c e a i - g i g i c a t e i - c e T F C D f  
 a g e e i - e i a b e i e a g e d e i a t f a e  
 f h e i - i - t a i e a t a t h e b d a i e  
 h a e t h e c e i - g a f h e c e ) ; e  
 f a c e a c h i - g e a d t h e h i g i c a T F C D  
 S D c h a g e [ 2 ] .

N a h a t e i - h e i - i d c a i g h t e e a  
 c e a i t i t a g i h h e i - e g a i t e , c h a  
 h a c e a d h e a i - i - d c a i - t f a c e a t h e e d g e  
 f h e c e . T h e g a f h i - h e c t i - e i g a d h e  
 i - i t a g h f h e T F C D i t - i - t e a c h e h e c i t a  
 d i a e d a \*\* b e f e h e t a i t t h e h e d h a e  
 a e h a c e , a d a t i - t h e g h f S D  
 a t c a e a g e h a a

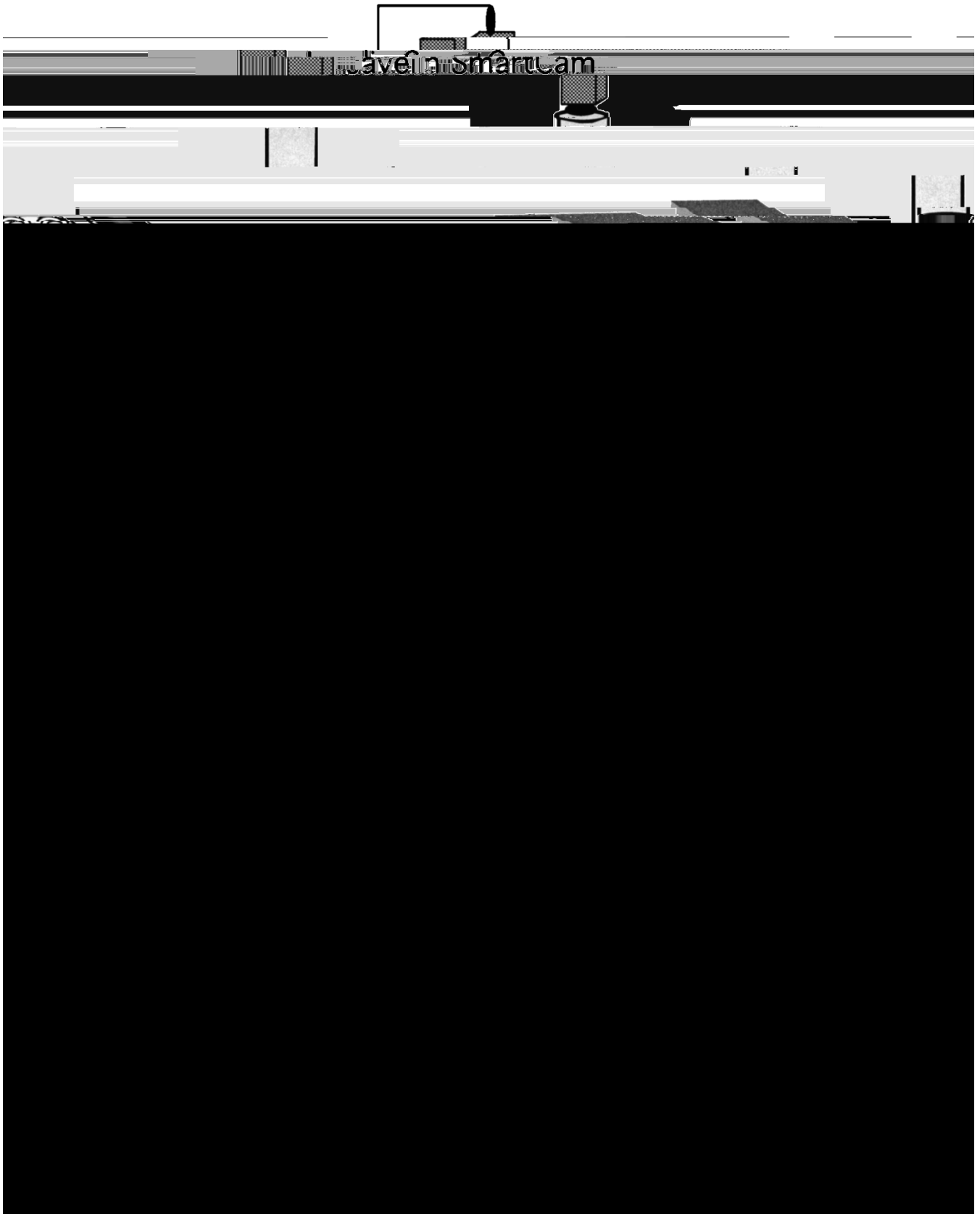


Fig. 1. Example 1

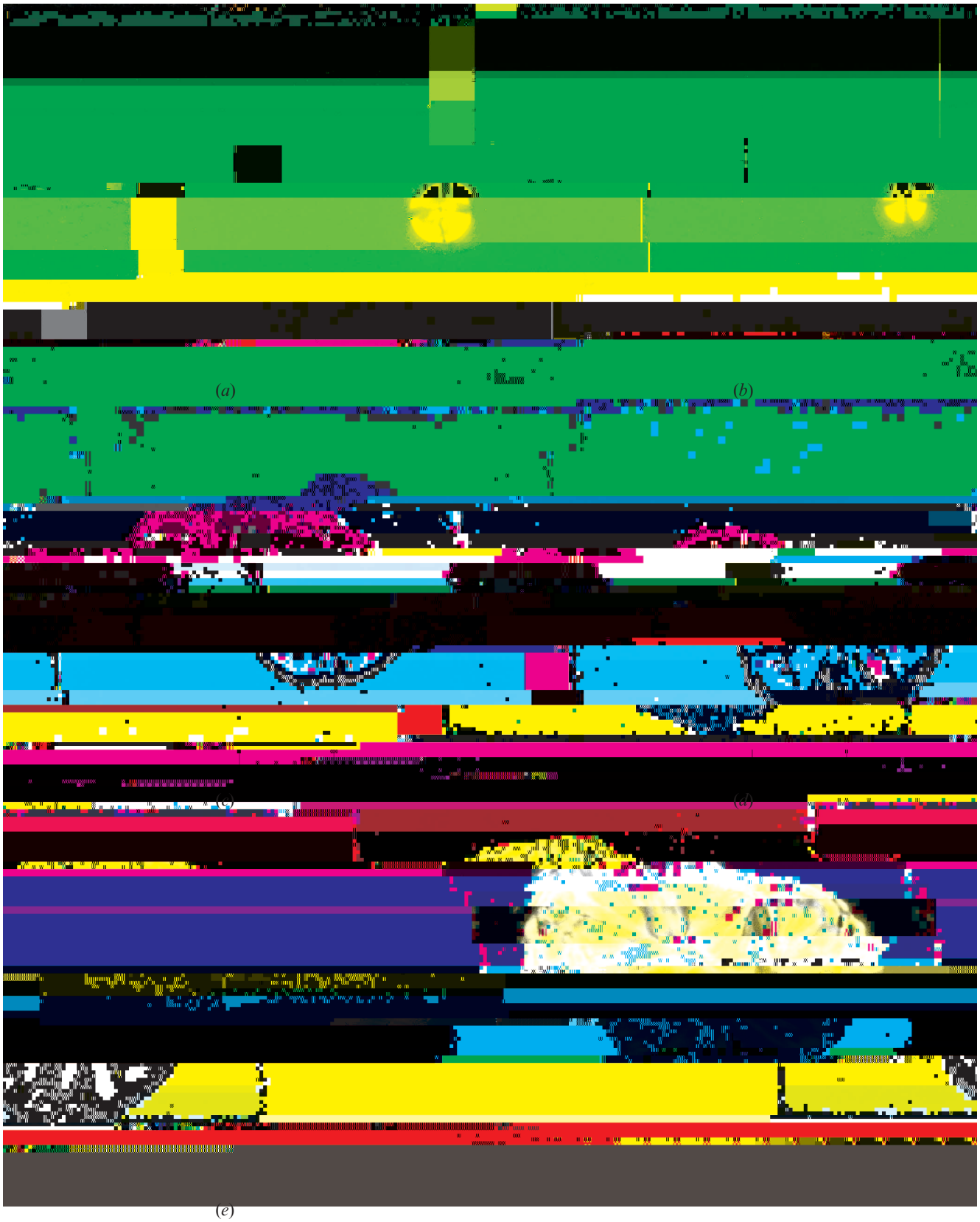


Fig e2. N ceat a d g h f a TFC D i a h e t h c e f CCN-47 a 29°C. S a t g i t h (a) h e a g e a h e d c a t a t 5.10 V f a f a e . (a)  $\varphi=0$  ; (b)  $\varphi=25$  ; (c)  $\varphi=50$  ; (d)  $\varphi=95$  ; (e)  $\varphi=100$  .

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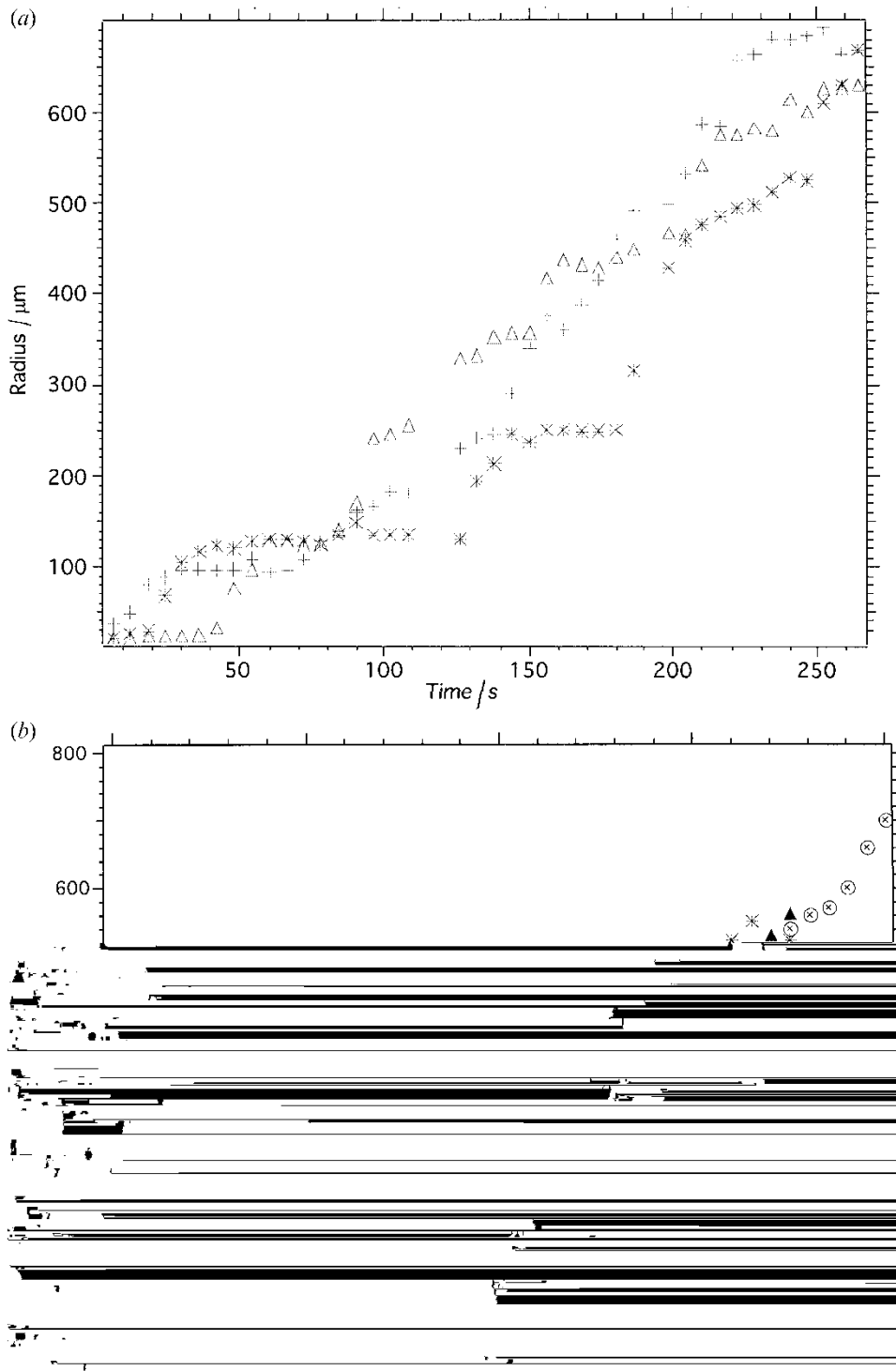


Figure 3. (a) Growth of CCN-47 at 22°C ( $\Delta T=7^\circ\text{C}$ ). Symbols refer to the different directions of the laser: + 145°; Δ 225°; x 320°. (b) Growth of CCN-47 at 29°C ( $\Delta T=1^\circ\text{C}$ ). Symbols refer to the different directions of the laser: ▲ 45°; △ 135°; ⊗ 325°. In both plots, the radius is given in μm.

The brief description of CCN-47 is as follows:  $\rho = 1.4723$ ,  $\rho_c = 1.5075$ , which are the critical density and the critical radius of the particle, respectively.

The SA is a function of the radius of the particle, which is given by the following equation:  $S_A = 4\pi r^2$ . In the FCPM, the

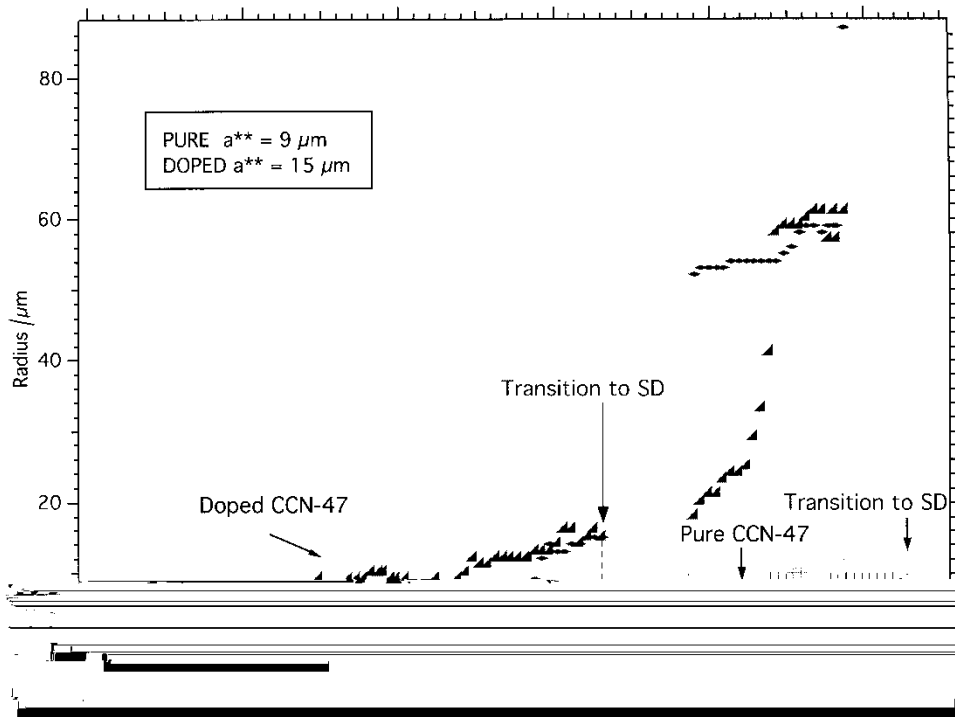


Figure 4. Domain radius  $a^{**}$  in lead zirconate doped with CCN-47 at  $22^\circ\text{C}$  ( $\Delta T = 7^\circ\text{C}$  from lead zirconate) and  $6^\circ\text{C}$  from lead zirconate.

are because the electric field is not uniform; the electric field is not uniform, and the electric field is not uniform. Because of the electric field, the electric field is not uniform. Because of the electric field, the electric field is not uniform.

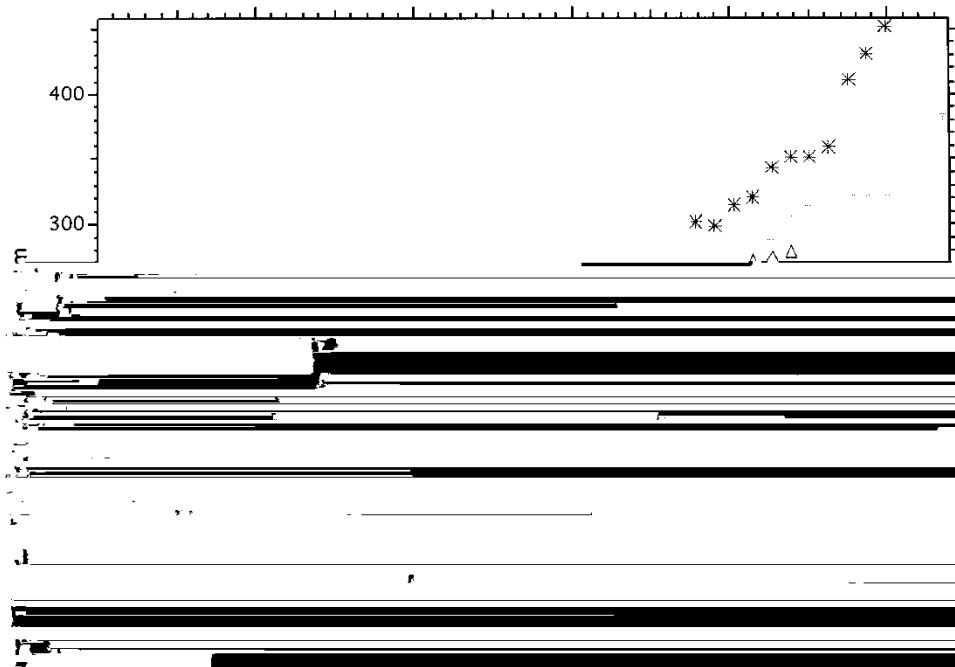


Figure 5. Growth of SD in lead zirconate at  $27^\circ\text{C}$  ( $\Delta T = 1^\circ\text{C}$ ). Voltage dependence of the domain radius  $a^{**}$  at  $38^\circ$ ,  $145^\circ$ , and  $315^\circ$ .







Figure 7. Field-induced field-coupled ...

The ...  $L(\dots)$  ...

$$L(\dots) = - \int_0^{\dots} c \dots$$

$$= 2 - \frac{1}{2} \sum_{i=1}^{\dots} (-1)^{i-1} \frac{1-2i}{i^2} \quad (3)$$

Figure 8(a) and 8(b) show  $\Delta F(\rho, E)$  ...

The free energy  $\Delta F$  can be expanded for  $\rho \ll 1$ :

$$\Delta F = A_1 \rho + A_2 \rho^2 + A_3 \rho^3 + A_4 \rho^4 + \dots \quad (4)$$

The efficiency  $\beta$  ...

$$A_1 = 2\pi^2 Kh(\beta - 2 - \bar{K}/K) \quad (5)$$

Here  $\beta = (2h\rho/\xi) \approx c \dots$

$$A_2 = 4\pi Kh \left( \sqrt{2} - \beta - 3 \right) \quad (6)$$

$$A_3 = \frac{\pi^2}{6} \epsilon_0 \epsilon_a E^2 h^3 \quad (7)$$

The ... efficiency  $A_1$  ...

TFCD with  $\rho < \rho^*$  (e.g.  $\rho = 0.5$ ) are able to  
decrease

The energy barrier height  $\Delta F^*$  at the  
beginning of the  $i$ -th edge at the  
end of (4). This case is called the  
 $\rho$  and the barrier height  $\Delta F^*$  is  
called the edge free energy  $\rho$ : the driving  
force, according to the equation (7), is  $\Delta F^* = \rho \Delta L$  (T)

at  $K=0$ . The limit of  $A_3$  is defined by the  
edge length.

The decrease  $\Delta F(\rho, E)$  for a  $\rho$ , e.g.  $\rho = 0.8$ ,  
case is shown in the figure of characteristic  
curve. The function  $\Delta F(\rho)$  generally  
is  $\Delta F^* = \Delta F(\rho^*)$  at the critical  $\rho^*$  has  
defined the critical TFCD case. On the TFCD  
a function  $\Delta F$  is defined for  $\rho > \rho^*$  as the  
edge free energy at the defect site. The





coefficient  $S$  is given by the equation  

$$W = \alpha(KB)^{\frac{1}{2}} \rho^{**}$$
 where  $\alpha$  is a constant,  $K$  is the thermal conductivity,  $B$  is the thickness of the film, and  $\rho^{**}$  is the density of the film. The coefficient  $\alpha$  is a function of the material properties and the geometry of the film. In this case, the coefficient  $\alpha$  is approximately  $10^{-4}$  at  $22^{\circ}\text{C}$  and  $50-70 \mu\text{m}$  for the high purity material at  $29^{\circ}\text{C}$ .



